

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	2	evaluat\$3 same pattern same feature adj index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:20
S2	1	evaluat\$3 adj pattern same feature adj index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:20
S6	129	evaluat\$3 same pattern and feature same index and device same property	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:22
S5	814	evaluat\$3 same pattern and feature same index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:22
S4	28	evaluat\$3 same pattern and feature adj index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:22
S7	49	evaluat\$3 same pattern and feature same index and device same property and electron with beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:24
S8	46	evaluat\$3 same pattern and feature same index and device same property and electron with beam and dimension	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:25
S9	9	evaluat\$3 same pattern and feature same index and device same property and electron with beam and dimension\$2 with shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:27

## EAST Search History

S10	63	(calculat\$3 evaluat\$3 quantif\$4) and pattern and feature same index and device same property and electron with beam and dimension\$2 with shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:36
S13	37	(calculat\$3 evaluat\$3 quantif\$4) and pattern and feature same index and device same property and electron with beam and (three adj3 dimension\$2 3D 3-D) same shape and process and scan\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:38
S12	39	(calculat\$3 evaluat\$3 quantif\$4) and pattern and feature same index and device same property and electron with beam and (three adj3 dimension\$2 3D 3-D) same shape and process	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:38
S11	40	(calculat\$3 evaluat\$3 quantif\$4) and pattern and feature same index and device same property and electron with beam and (three adj3 dimension\$2 3D 3-D) same shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:38
S14	0	738/714.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 17:56
S15	37969	index same feature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 17:57
S16	1986	pattern same (tree adj2 dimension 3D 3-D) same shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 17:58
S18	15	S15 and S16 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 17:59

## EAST Search History

S17	359586	property same (device circuit )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 17:59
S19	2016083	control\$4 same process\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:01
S20	12	S18 and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:02
S21	12037	electron adj beam and (SEM scanning adj electron adj microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:03
S23	40	index adj feature same pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:04
S22	2	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:04
S25	9	index adj feature same pattern and dimension\$2 and property	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:05
S24	28	index adj feature same pattern and dimension\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:05

## EAST Search History

S26	7	index adj feature same pattern and dimension\$2 and property and device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:06
S28	3	detect\$3 with abnormal same pattern and feature adj index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:07
S27	2330	detect\$3 with abnormal same pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:07
S29	353	detect\$3 with abnormal same pattern and property and (device transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:08
S30	97	detect\$3 with abnormal same pattern and property and (device transistor) and three adj2 dimension\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:09
S32	52	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:10
S31	57	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:10
S33	50	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:11

## EAST Search History

S34	49	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:12
S35	12	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:17
S36	12	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and index and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:18
S37	44	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:19
S38	25	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:22
S40	13	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:25
S42	9	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3 and relation\$4 and waveform	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:27

## EAST Search History

S43	9	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3 and relation\$4 and waveform and (calculat\$3 estimat\$3 evaluat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:29
S44	9	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3 and relation\$4 and waveform and (calculat\$3 estimat\$3 evaluat\$3) and signal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:30
S45	4	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3 and relation\$4 and waveform and (calculat\$3 estimat\$3 evaluat\$3) and signal and (area size) same region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:31
S41	13	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and scatter\$3 and relation\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:34
S39	23	detect\$3 with (defect abnormal) same pattern and property and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:43

## EAST Search History

S49	3	detect\$3 with (defect abnormal) same pattern and property same (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:45
S51	46	detect\$3 with (defect abnormal) and pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:46
S50	38	detect\$3 with (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:46
S52	52	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 18:53
S53	39	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and (electrical adj characteristic property )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:17
S54	48	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and (electrical adj characteristic property threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:30



## EAST Search History

S55	2	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and estimat\$3 with (electrical adj characteristic property threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:32
S56	9	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4) and feature and wafer and irradiat\$3 and estimat\$3 same (electrical adj characteristic property threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:36
S57	48	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor circuit IC) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4 estimat\$3) and feature and wafer and irradiat\$3 and (electrical adj characteristic property threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:37
S58	8	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor circuit IC) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4 estimat\$3) and feature and wafer and irradiat\$3 and (estimat\$3 calculat\$3) with (electrical adj characteristic property threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:42
S59	6	(inspect\$3 detect\$3) same (defect abnormal) same pattern and (device transistor circuit IC) and three adj2 dimension\$3 and electron adj beam same scan\$4 and (calculat\$3 evaluat\$3 quantif\$4 estimat\$3) and feature and wafer and irradiat\$3 and (estimat\$3 calculat\$3) with (electrical adj characteristic threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:46



## EAST Search History

S60	18	pattern and (device transistor circuit IC) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4 estimat\$3) and feature and wafer and irradiat\$3 and (estimat\$3 calculat\$3) with (electrical adj characteristic threshold adj voltage leakage adj current delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:47
S61	10	pattern and (device transistor circuit IC) and three adj2 dimension\$3 and electron adj beam and scan\$4 and (calculat\$3 evaluat\$3 quantif\$4 estimat\$3) and feature and wafer and irradiat\$3 and (estimat\$3 calculat\$3) with (electrical adj characteristic threshold adj voltage leakage adj current )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:48
S66	74	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:53
S69	66	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and dimension\$3 and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:54
S68	66	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and dimension\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:54
S67	74	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:54
S70	43	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:55

## EAST Search History

S71	8	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape and irradiat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 19:57
S72	43	(calculat\$3 estimat\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 20:07
S83	46	(calculat\$3 estimat\$3 extract\$3) with (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 20:08
S84	75	(calculat\$3 estimat\$3 extract\$3) same (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 20:09
S85	57	(calculat\$3 estimat\$3 extract\$3) same (electrical adj characteristic property) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 20:14
S88	123	(calculat\$3 estimat\$3 extract\$3) with (electrical adj characteristic property value resistance) same pattern and feature and shape and electron adj beam and (circuit device) and three adj2 dimension\$3 and shape and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 20:20
S97	66	evaluat\$3 with pattern with process\$3 and (3-D threee adj2 dimension) and feature and shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:00
S98	63	evaluat\$3 with pattern with process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:02

## EAST Search History

S99	32	evaluat\$3 with pattern with process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and (extract\$3 ) same (electrical chractersitic value capacitance resistance voltage current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:03
S100	5	evaluat\$3 with pattern with process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and (extract\$3 ) same (electrical chractersitic value capacitance resistance voltage current) and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:04
S101	13	evaluat\$3 same pattern same process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and (extract\$3 ) same (electrical chractersitic value capacitance resistance voltage current) and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:06
S102	15	evaluat\$3 same pattern same process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and (extract\$3 estimat\$3 calculat\$3) same (electrical chractersitic value capacitance resistance voltage current) and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:08
S106	22	(measur\$3 estimat\$3 calculat\$3 extract\$3)same (property characteristic value current voltage capacitance resistance electric\$2) same pattern same process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and wafer and (electron adj beam irradiat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:50
S107	25	(measur\$3 estimat\$3 calculat\$3 extract\$3 inspect\$3)same (property characteristic value current voltage capacitance resistance electric\$2) same pattern same process\$3 and (3-D threee adj2 dimension) and feature and shape and (circuit device) and wafer and (electron adj beam irradiat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 11:51

## EAST Search History

S13 9	30	regression adj analysis and pattern same( monitor\$3 inspect\$3) and feature same index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 10:48
S14 5	14	regression adj (function analysis) same pattern same shape	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/13 18:14
S15 1	60	regression adj analysis and pattern and shape and feature with index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/13 18:59
S14 0	35	regression adj analysis and pattern same shape and ( monitor\$3 inspect\$3) and feature same index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/13 19:02
S15 9	36	regression adj analysis and pattern and inspect\$5 and feature and index and irradiat\$5 and electron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/13 19:08
S16 9	183	regression adj analysis and pattern and feature and irradiat\$5 and electron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/13 19:19
S1	2	"20040156223" and feature adj index	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:18
S17 0	2239	716/4.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:51

## EAST Search History

S17 2	297	S170 and S171	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:54
S17 4	3	S172 and S173	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:55
S17 3	21236	irradiat\$5 and electron with beam and scan\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:55
S17 5	14256	(pattern feature) same (width index) and database	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:57
S17 1	71362	(pattern feature) and (width index) and database	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:57
S17 6	79	S170 and S175	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:01
S17 7	1656	716/5.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:31
S17 8	0	S171 and S173 and 716/5.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:33

## EAST Search History

S17 9	3068	250/311.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:34
S18 0	31	S171 and 250/311.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:36
S18 1	18	S171 and S173 and 250/311.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:38